Automotive Power Electronics Roadmap

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Automotive applications for power electronics is increasing rapidly due to the demand for hybrid and future fuel-cell powered vehicles. The power electronic systems are not only required for driving the vehicle (Fig. 1) but are also used to interface energy storage components and to supply high power auxiliary systems such as active suspension, electric valves and air conditioning units. The automotive industry has specific requirements for its power electronic systems such as a compact design, high reliability, long life time and an extremely low cost to power ratio. The systems are further required to operate over a wide ambient temperature range and with liquid cooling temperatures of typically 105°C. In a study from the USA FreedomCAR project, it is projected that the required cost of the power electronic systems has to reduce by a factor of three until the year 2020.

The task of the Automotive Roadmap Committee was to clarify which technologies are needed to achieve the performance and cost targets of the automotive industry. The road mapping effort focused on three systems as circled in Fig. 1:

- 1. a non-isolated dc-dc converter, in the 40 to 100 kW power range, that can be used as a fuel cell interface,
- 2. an ac-dc inverter that is integrated into the machine housing of a hybrid drive system (since an

integrated solution provides the greatest cost reduction potential), and,

3. an isolated dc-dc converter to provide bidirectional power flow between the high voltage bus and the 14 V accessory power system, where the required power range is 1 to 3 kW.

The main outcomes of the road mapping exercise are that the drive inverter cost target could potentially be meet if the power electronics is integrated, and that the maximum achievable power density of the non-isolated dc-dc converter and the isolated dc-dc converter is 50 kW/liter and 10 kW/liter respectively.

The road mapping process utilized a bottom-up approach. Here, mathematical descriptions for the electrical, thermal, packaging and magnetic components are developed. Using these descriptions a component technology space is formed. By using the specifications, topologies, and operating parameters the component space can be optimally mapped into a system performance space, which gives system performance measures such as efficiency, power density and costs. Exploring the performance, and then undertaking a reverse mapping from this new point back into the component space, provides information on how the technologies must be developed to achieve the new desired system performance.



Fig. 1 Power electronic key systems for the cars of tomorrow. The three considered systems in the automotive power electronics road mapping exercise are encircled in yellow.







Automotive Power Electronics Research Roadmap Initiative

Coordinators

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supported by

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Outline

- **General Considerations**
- Si / SiC Inverter
 Non-Isolated DC/DC Converter
 Isolated DC/DC Converter
 High Temperature Gate Drive
 Optimization



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Power Electronic Key Systems for the Cars of Tomorrow





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Inverter

Topologies DOF for Optimization Technologies



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Electric Drive for Hybrid Traction



Alternative Topologies





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Z-Source Inverter





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DOF for Optimization



Optimization on System Level





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Traction Drive Inverter





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Traction Drive Inverter

Total Material Costs



Results

- IGBT is the preferred technology for traction voltages above about 150V
- Total inverter cost, package volume, and losses decrease with increasing traction voltage when using IGBTs
- The inverter becomes considerably less expensive in the case of a constant traction voltage (k_v=1)



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Electric Drive for Hybrid Traction





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Comparative Evaluation of SiC for DC/DC Converter



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Switching Transient Shaping



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Minimization of Parasitics LeCroy U_{DS} 100V/Div I_{DS} 10A/Div Passive Damping ► Gate Drive / Active Damping § 50 ns 1.00 V 4 50 ns 100 V **PCB Damping Layer** 50ns/Div LeCroy U_{DS} 100V/Div C_{Lboost} $C_{j,D}$ L_{wire} $L_{boost} I_{DS} \leftarrow$ D_1 C_{in} V_{in} V_{out} 'oss $V_{\scriptscriptstyle DS}$ I_{DS} V_{gate} 10A/Div A 50 ns 100 V 🔓 50 ns 1.00 V L_{wire} ETH Eidgenössische Technische Hochschule Zürich Swiss Federal Institute of Technology Zurich

Without Damping Layer



Thermo-Mechanical Reliability



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Thermo-Mechanical Reliability 250 Source: Lu / VPEC Temperature (°C) 200 **SiC Power Device Assembly Low Temperature Sintered Silver** 150 **Die Attachment** 100 ► Thermal Cycling 50°C 250°C ► 6'000 TC Survived 50 10 5 0 15 20 Time (mins) = Al₂O₃ DBC 45 · AIN DBC 40 Bonding strength (MPa) 35 **Die-Shear Test** 30 25 20 SiC power device 15 Sintered silver Coated silver or gold 10 Coated nickel **DBC** copper 5 **Direct-Bond-Copper** Al₂O₃ or AIN ceramic base n DBC copper 500 1000 2000 4000 6000 0 8000 Number of thermal cycles ЕТН Eidgenössische Technische Hochschule Zürich Swiss Federal Institute of Technology Zurich





Non-Isolated DC/DC Converter

—— Overlapping Input/Output —— Voltage Ranges



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Traction Voltage Converter





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Bi-Directional DC/DC Converters for Overlapping Voltage Rages

Cascaded Boost-Buck Converter

Cascaded Buck-Boost Converter



Large Passive Components Count

- 3 Capacitors
- 2 Inductors

Minimum Passive Components Count
• 2 Capacitors

• 1 Inductor



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Cascaded Buck-Boost Converter





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Converter Module Hardware





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Overall Efficiency vs. Output Power





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Ultra-Compact Converter Module







Isolated High Temperature SiC J-FET Gate Drive Circuit





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Phase Difference Circuit

Proposed by D.C. Hopkins, Univ. at Buffalo, USA



- ► Vs Product: Bipolar transformer output voltage
- ► Capacitor C_g to perserve JFET gate voltage during MOSFET S₁ or S₂ Off-Time



Advantages and Drawbacks

- No Duty-Cycle limitation (static Turn-Off)
- High switching speeds (MOSFET half-bridge)
- High complexity
- High costs



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Edge-Triggered Driving Circuits



Size of Capacitor C_g

- Large capacitances reduce switching speed
- Large capacitances cause significant losses
- Small capacitances limit Off-Time

Second winding due to auxiliary switch U_{as} limits



Advantages and Drawbacks

- Moderate Active Component Count
- High Switching Speeds
- Large Duty-Cycle Range (1% ... 100%)
- (Off-Time limited by capacitor size)
- special pulse pattern to provide negative bias useable



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Experimental Results





Edge-Triggered Circuit shows Excellent Performance



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Isolated DC/DC Converter

____ Dual Active Bridge Magnetically Integrated Current Doubler



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Prototype of the Dual Active Bridge



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Experimental Results





Efficiency Increased by 10% at 2kW Output Significantly Higher Efficiency at Partial Load



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Isolated DC/DC Converter

____ Magnetically Integrated _____ Current Doubler



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Current Doubler with Integrated Magnetics



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Enabling Technologies Identified in Copenhagen Roadmap Meeting

- Advanced Cooling of Power Semiconductors
- Increased Thermal Cycling Capability / Increased ΔT_{i-c}
- Advanced Packaging Materials
- Advanced Cooling of Passives
- High Current Low HF Loss Interconnection Technologies
- Local EMI Shielding / Filtering
- Integration of Gate Drives and Sensors etc.
- Reliability / Robustness Test Procedures
- Multi-Domain Design / Optimization Platform





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System Optimization

Pareto-Optimal Design Technology Vectors Sensitivities



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Bottom-Up Roadmap Approach for Power Electronic Systems

- ► How to Identify Future Key Technologies / Required Progress ?
- 1. Clarify State of the Art & Mapping of Component Technologies into System Performance

Demonstrator Systems

- 2. Define Goal as Resulting from *Top-Down Analysis*
- 3. Analyze Sensitivities
- 4. Identify Most Influential Technologies
- 5. Derive Required Progress in Specific Technology Metrics / FOM



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Sensitivities & Technology Vectors

